N-Channel Enhancement Mode Power MOSFET

Description

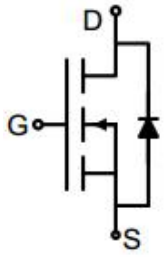
The GT016N10TL uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

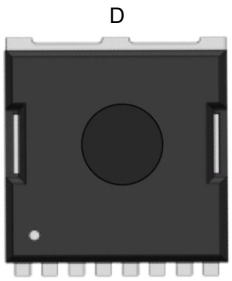
- V_{DS} 100V
- I_D (at V_{GS} = 10V) 362A
- $R_{DS(ON)}$ (at V_{GS} = 10V) < 1.5mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



G_1 S_2 S_3 S_4 S_5 S_6 S_7 S_8

TOLL-8L

Ordering Information

Device	Package	Marking	Packaging
GT016N10TL	TOLL-8L	GT016N10	2000pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	100	V
Continuous Drain Current	T_C = 25ºC	I_D	362	A
	T_C = 100ºC		229	
Pulsed Drain Current (note1)		I_{DM}	1448	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D	380	W
Single pulse avalanche energy （note2）		E_{AS}	812	mJ
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	40	ºC/W
Maximum Junction-to-Case	R_{thJC}	0.33	ºC/W

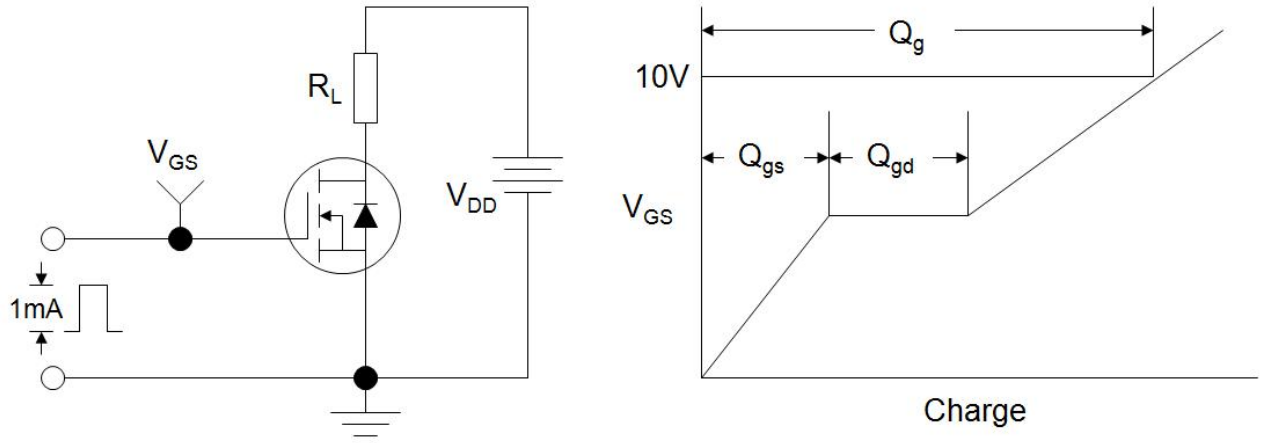
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100V, V_{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0	3.0	4.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 15A	--	1.35	1.5	mΩ
Forward Transconductance	g_{FS}	V_{GS} = 5V, I_D = 15A	--	83	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 0.5MHz	--	9200	--	pF
Output Capacitance	C_{oss}		--	3700	--	
Reverse Transfer Capacitance	C_{rss}		--	100	--	
Total Gate Charge	Q_g	V_{DD} = 50V, I_D = 15A, V_{GS} = 10V	--	165	--	nC
Gate-Source Charge	Q_{gs}		--	33	--	
Gate-Drain Charge	Q_{gd}		--	48	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 50V, I_D = 15A, R_G = 4.5Ω	--	29	--	ns
Turn-on Rise Time	t_r		--	64	--	
Turn-off Delay Time	$t_{d(off)}$		--	120	--	
Turn-off Fall Time	t_f		--	106	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	362	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 15A, V_{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Qrr	I_F = 15A, V_{GS} = 0V di/dt=100A/us	--	166	--	nC
Reverse Recovery Time	Trr		--	91	--	ns

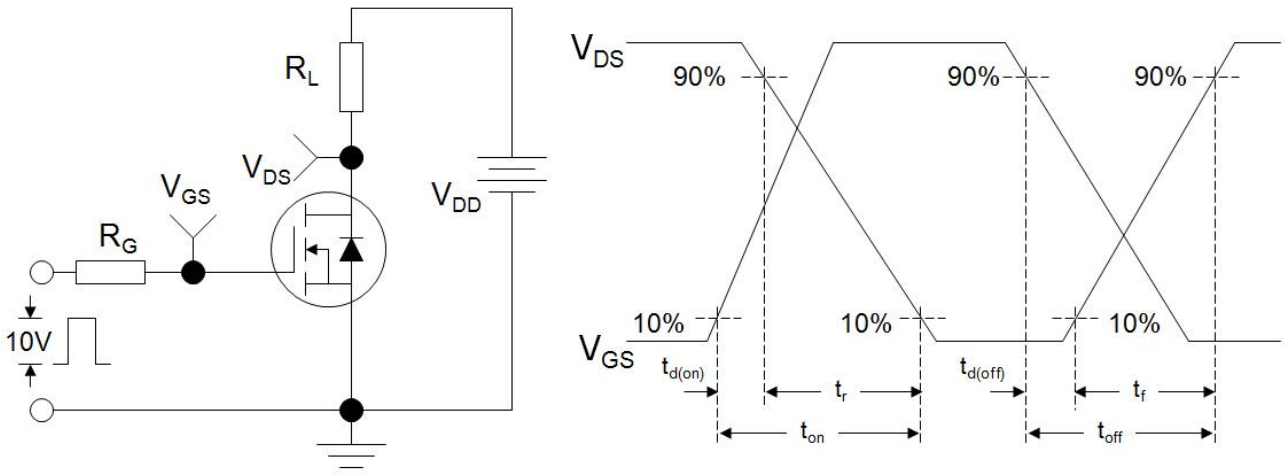
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=50V,VGS=10V,L=0.5mH,Rg=25Ω
   The table shows the minimum avalanche energy, which is 1650mJ when the device is tested until failure
3. Identical low side and high side switch with identical R_G

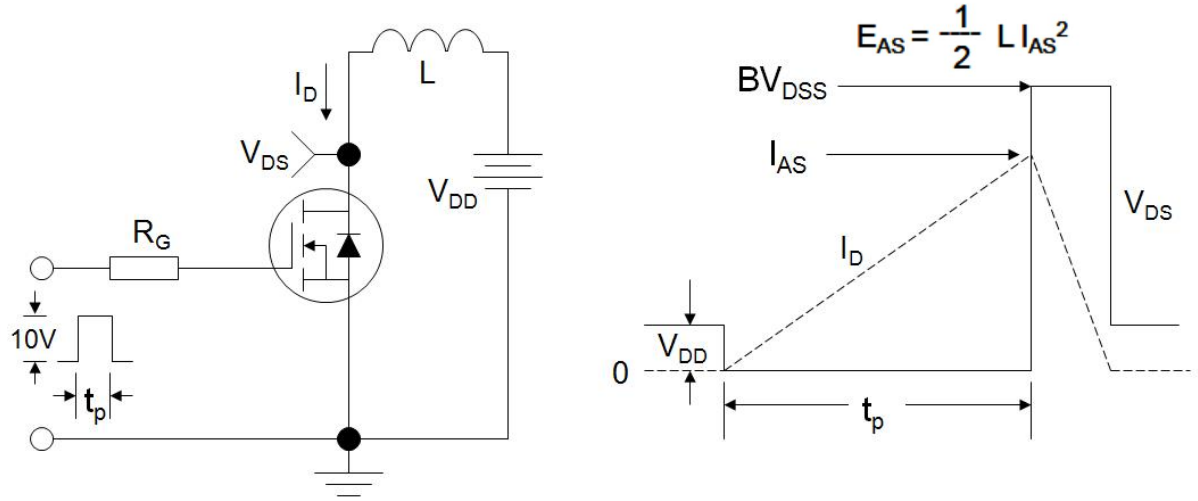
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

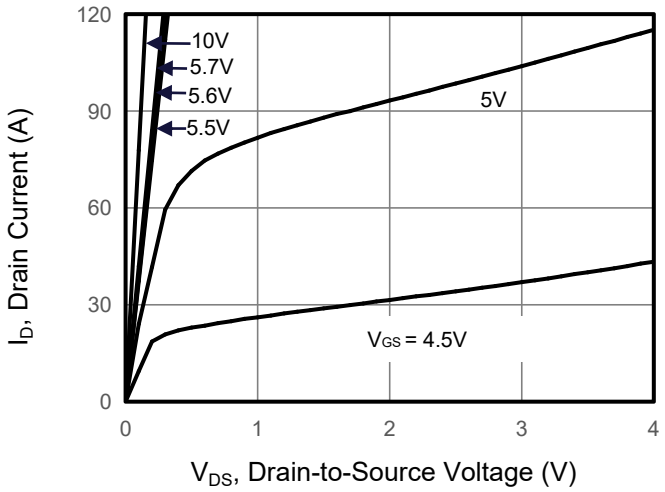


Figure 2. Transfer Characteristics

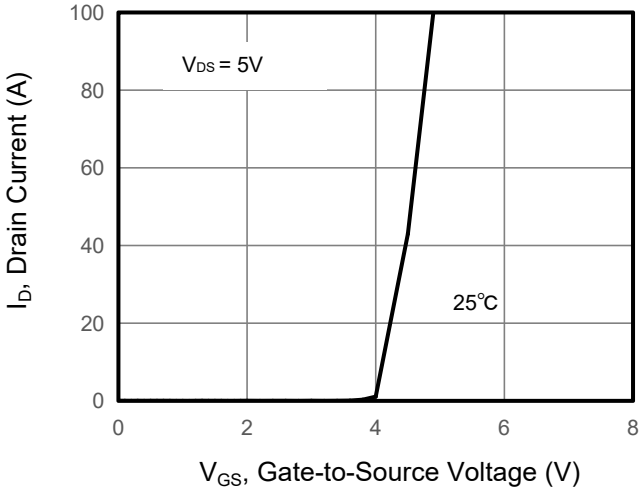


Figure 3. Drain Source On Resistance

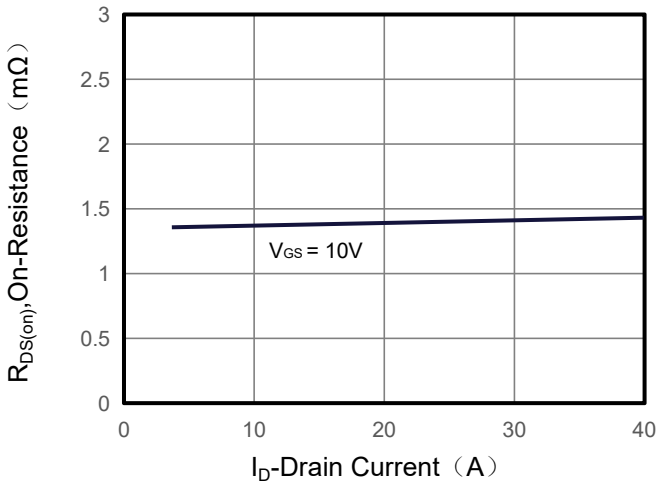


Figure 4. Gate Charge

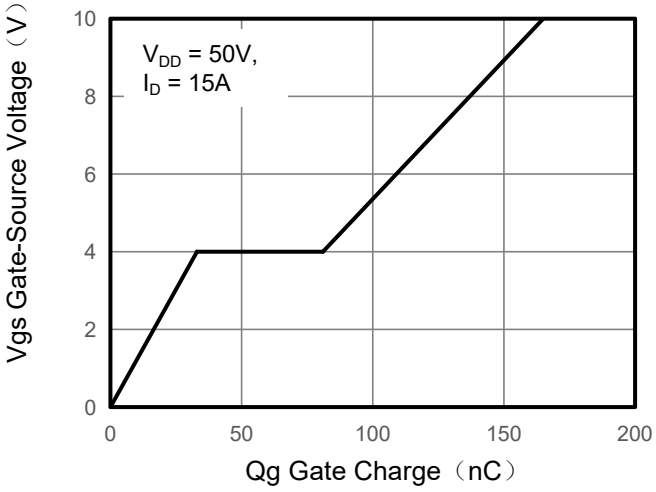


Figure 5. Capacitance

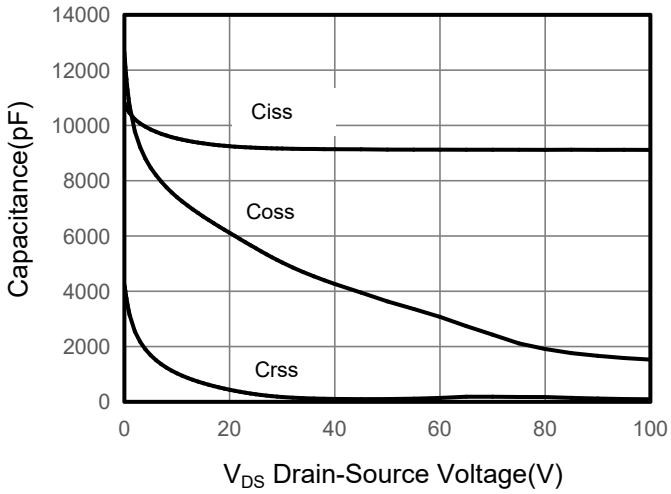
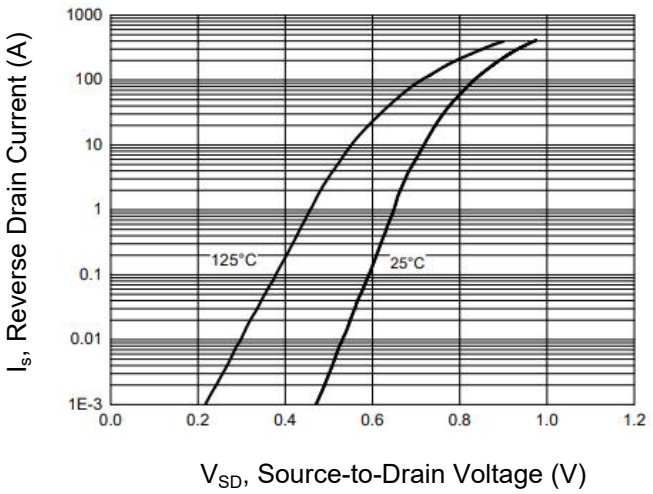


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

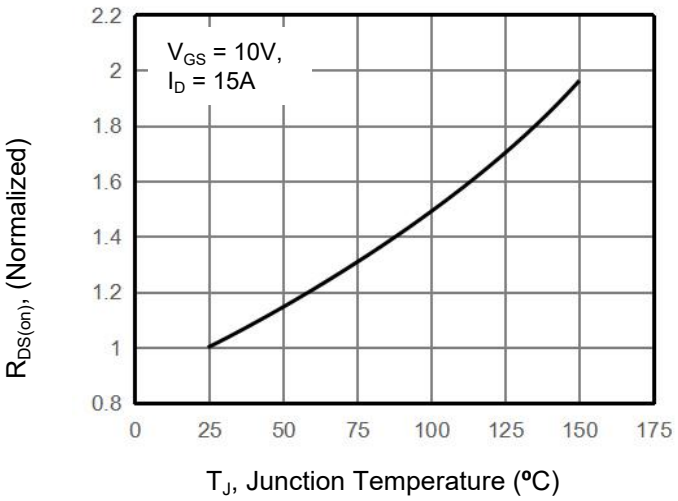


Figure 8. Safe Operation Area

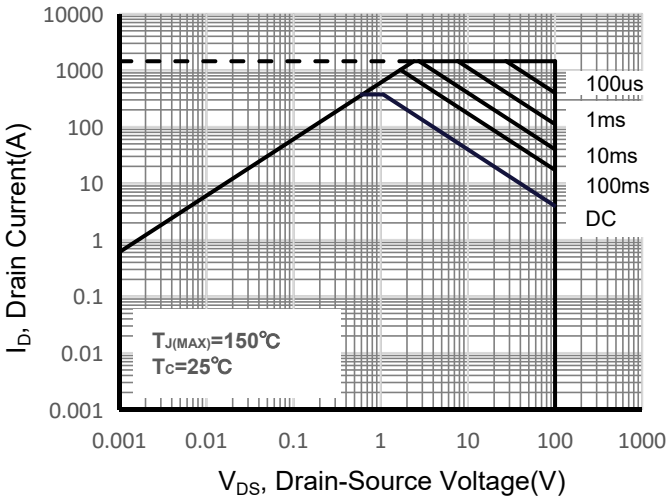


Figure 9. Maximum Continuous Drain Current vs Case Temperature

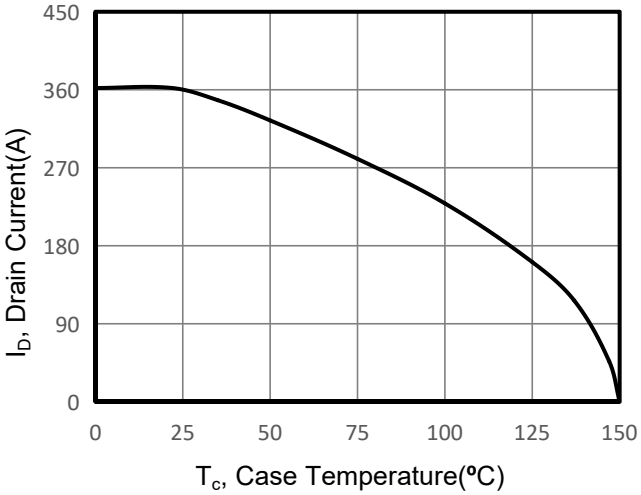
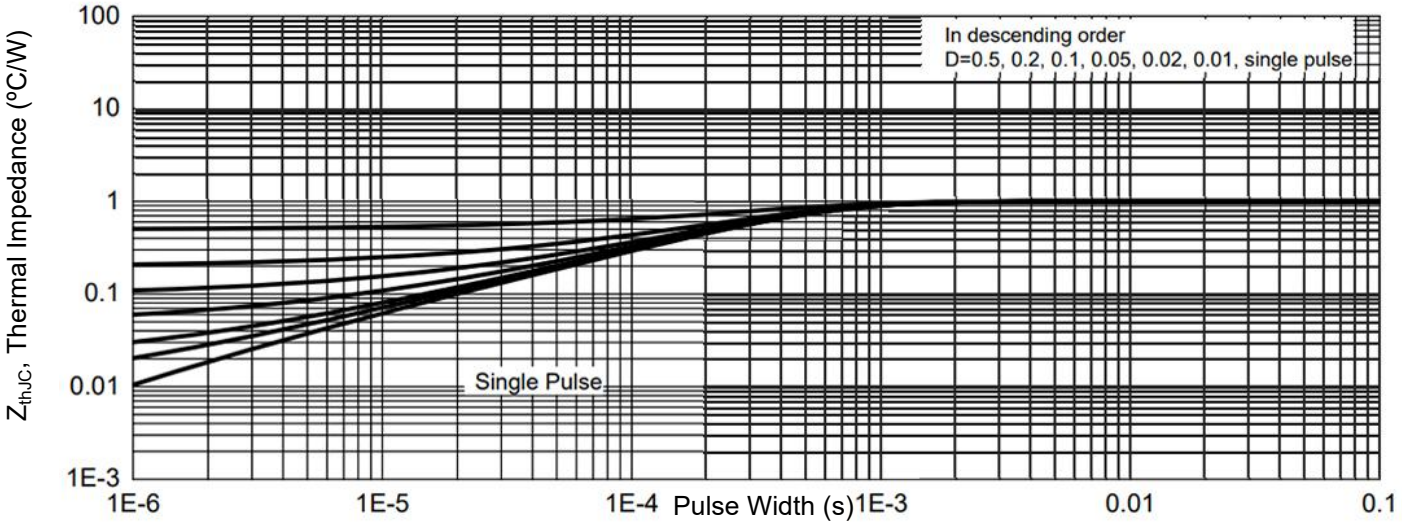
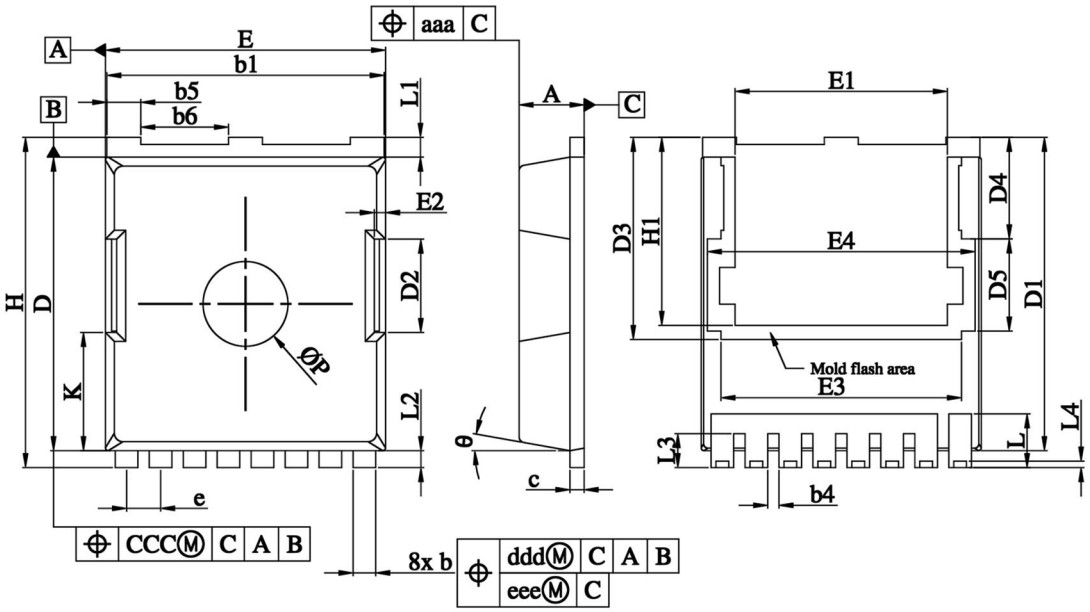
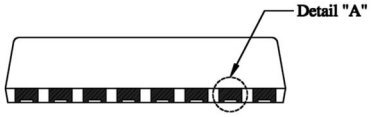


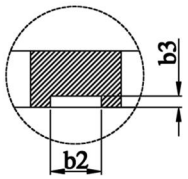
Figure 10. Normalized Maximum Transient Thermal Impedance



TOLL Package Information





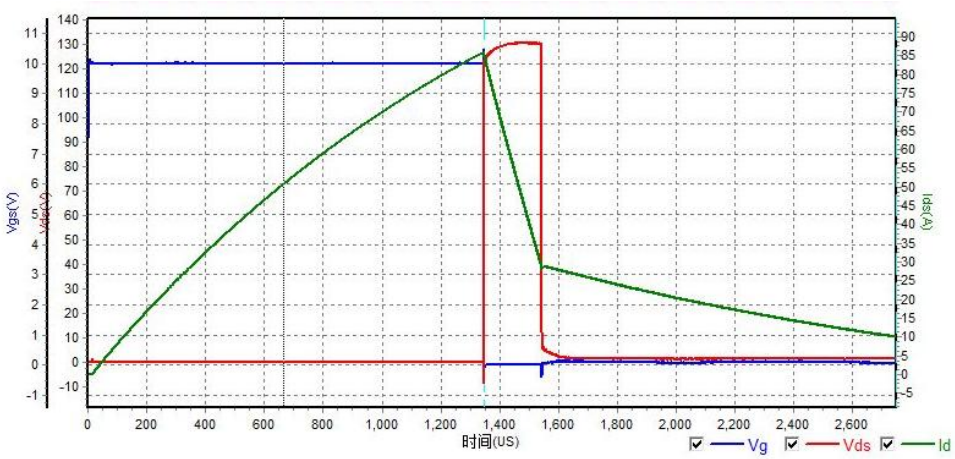


SYMBOL	COMMON MILLIMETER			SYMBOL	COMMON MILLIMETER		
	MIN.	NOMINAL	MAX.		MIN.	NOMINAL	MAX.
A	2.20	2.30	2.40	E2	0.30	0.40	0.50
b	0.70	0.80	0.90	E3		8.50	
b1	9.70	9.80	9.90	E4		9.46	
b2	0.36	0.45	0.55	H	11.50	11.68	11.85
b3	0.05	0.100	/	H1	6.55	6.65	6.75
b4	0.30	0.40	0.50	K	4.08	4.18	4.28
b5	1.10	1.20	1.30	L	1.60	1.90	2.10
b6	3.00	3.10	3.20	L1	0.50	0.70	0.90
c	0.40	0.50	0.60	L2	0.50	0.60	0.70
D	10.28	10.38	10.55	L3	1.00	1.20	1.30
D1	10.98	11.08	11.18	L4	0.13	0.23	0.33
D2	3.20	3.30	3.40	P	2.85	3.00	3.15
D3		7.15		θ		10° REF	
D4		3.59		aaa		0.20	
D5		3.26		ccc		0.20	
e	1.10	1.20	1.30	ddd		0.25	
E	9.80	9.90	10.00	eee		0.20	
E1	7.40	7.50	7.60				

Avalanche Current Graph

RPTI Condition:L=0.500mH,Vd=50.00V,Vg=10.00V,Vgr=0.00V,rg=25ohm					
	IAS		IAS		IAS
#1	81.361A	#2	82.988A	#3	83.641A
	82.124A		84.357A		84.386A
	83.446A		84.883A		85.013A
	84.009A		85.934A		86.048A
	FAIL		FAIL		FAIL

#1



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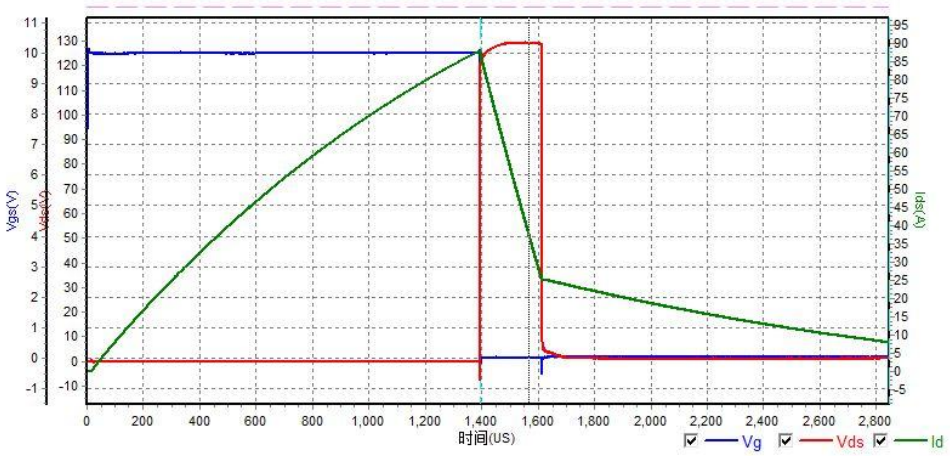

#3

